STP25N60M2-EP

N-channel 600 V, 0.175 Ω typ., 18 A MDmesh™ M2 EP Power MOSFET in a TO-220 package

Datasheet - production data

TAB

TO-220

Figure 1: Internal schematic diagram

D(2)

G(1)

S(3)

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Features

Order code	V_{DS} @ T_{Jmax}	$R_{DS(on)}$ max.	I_D
STP25N60M2-EP	650 V	0.188 Ω	18 A

- Extremely low gate charge
- Excellent output capacitance (C_{OSS}) profile
- Very low turn-off switching losses
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications
- Tailored for Very High Frequency Converters (f > 150 kHz)

Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 EP enhanced performance technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance, optimized switching characteristics with very low turn-off switching losses, rendering it suitable for the most demanding very high frequency converters.

Table 1: Device summary

Order code	Marking	Package	Packaging
STP25N60M2-EP	25N60M2EP	TO-220	Tube

This is information on a product in full production.

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Contents

1   Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at T_C = 25 °C	18	A
I_D	Drain current (continuous) at T_C = 100 °C	11.3	A
I_{DM}[1]	Drain current (pulsed)	72	A
P_{TOT}	Total dissipation at T_C = 25 °C	150	W
dv/dt[2]	Peak diode recovery voltage slope	15	V/ns
dv/dt[3]	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature	- 55 to 150	°C
T_j	Max. operating junction temperature		

Notes:

[1]Pulse width limited by safe operating area.

[2]I_{SD} ≤ 18 A, di/dt ≤ 400 A/µs; $V_{DS\ peak}$ < $V_{(BR)DSS}$, V_{DD} = 400 V.

[3]V_{DS} ≤ 480 V

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	0.83	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient max	62.5	°C/W

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	3.5	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25 °C, I_D = I_{AR}; V_{DD} = 50 V)	200	mJ

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 5: On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	600			V
I_{DSS}	Zero gate voltage Drain current	V_{GS} = 0 V, V_{DS} = 600 V			1	µA
		V_{GS} = 0 V, V_{DS} = 600 V, T_C = 125 °C			100	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 9 A		0.175	0.188	Ω

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS}= 100 V, f = 1 MHz, V_{GS} = 0 V	-	1090	-	pF
C_{oss}	Output capacitance		-	56	-	pF
C_{rss}	Reverse transfer capacitance		-	1.6	-	pF
$C_{oss\ eq.}$ [(1)](#)	Equivalent output capacitance	V_{DS} = 0 to 480 V, V_{GS} = 0 V	-	255	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, I_D = 0 A	-	7	-	Ω
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 18 A, V_{GS} = 10 V (see *Figure 16: "Gate charge test circuit"*)	-	29	-	nC
Q_{gs}	Gate-source charge		-	6	-	nC
Q_{gd}	Gate-drain charge		-	12	-	nC

Notes:

[(1)]$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7: Switching Energy

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{(off)}$	Turn-off energy (from 90% V_{GS} to 0% I_D)	V_{DD} = 400 V, I_D = 2 A R_G = 4.7 Ω, V_{GS} = 10 V	-	7	-	µJ
		V_{DD} = 400 V, I_D = 4 A R_G = 4.7 Ω, V_{GS} = 10 V	-	8	-	µJ

Table 8: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 9 A R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 15: "Switching times test circuit for resistive load"* and *Figure 20: "Switching time waveform"*)	-	15	-	ns
t_r	Rise time		-	10	-	ns
$t_{d(off)}$	Turn-off-delay time		-	61	-	ns
t_f	Fall time		-	16	-	ns

Table 9: Source drain diode
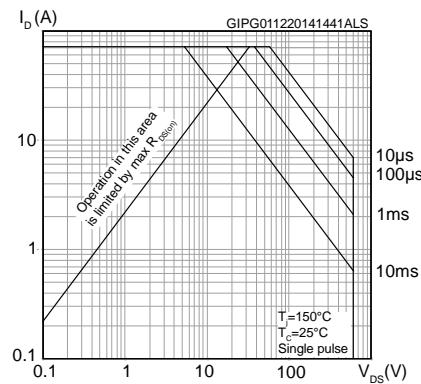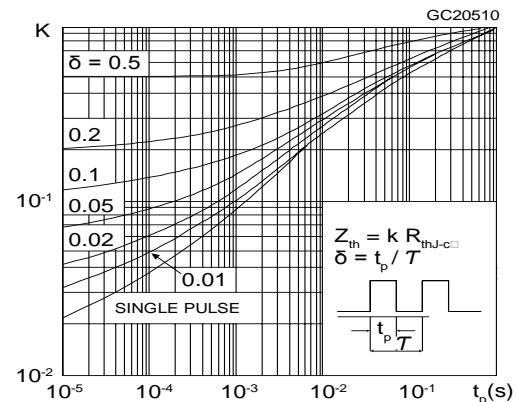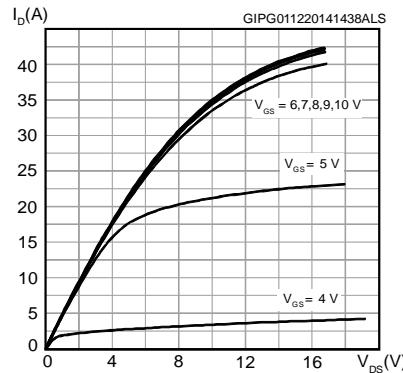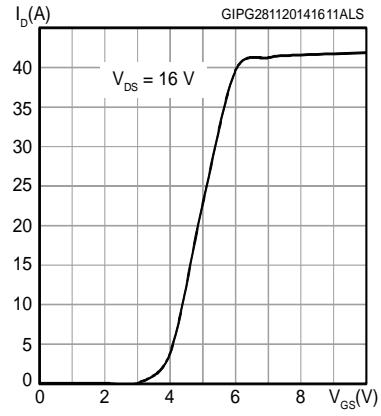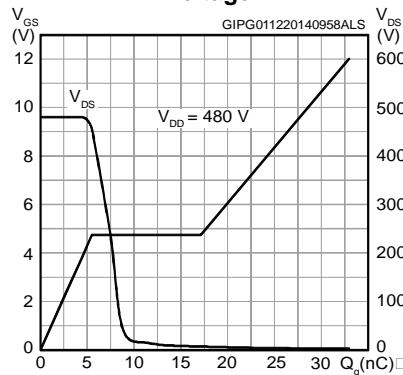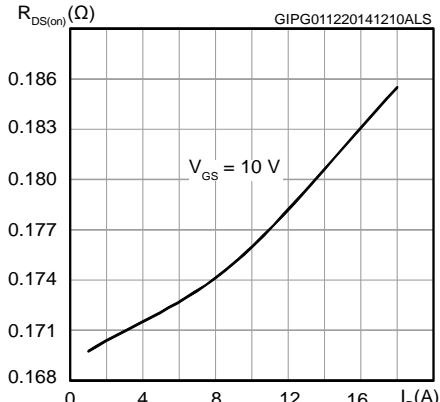
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		18	A
I_{SDM} [(1)]	Source-drain current (pulsed)		-		72	A
V_{SD} [(2)]	Forward on voltage	V_{GS} = 0 V, I_{SD} = 18 A	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 18 A, di/dt = 100 A/µs, V_{DD} = 100 V (see *Figure 17: " Test circuit for inductive load switching and diode recovery times"*)	-	360		ns
Q_{rr}	Reverse recovery charge		-	5		µC
I_{RRM}	Reverse recovery current		-	28		A
t_{rr}	Reverse recovery time	I_{SD} = 18 A, di/dt = 100 A/µs, V_{DD} = 100 V, T_j = 150 °C (see *Figure 17: " Test circuit for inductive load switching and diode recovery times"*)	-	445		ns
Q_{rr}	Reverse recovery charge		-	6.5		µC
I_{RRM}	Reverse recovery current		-	29		A

Notes:

[(1)]Pulse width is limited by safe operating area

[(2)]Pulsed: pulse duration = 300 µs, duty cycle 1.5%

2.2 Electrical characteristics (curves)

Figure 2: Safe operating area	Figure 3: Thermal impedance

Figure 4: Output characteristics	Figure 5: Transfer characteristics

| Figure 6: Gate charge vs gate-source voltage	Figure 7: Static drain-source on-resistance
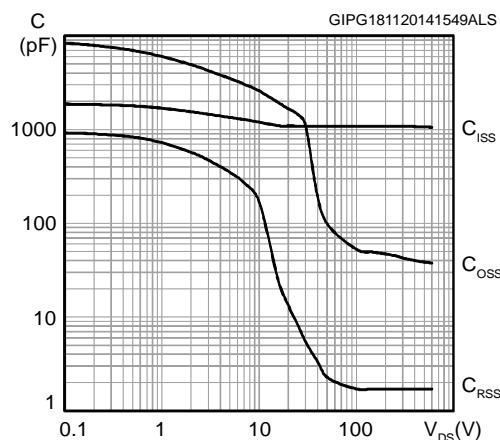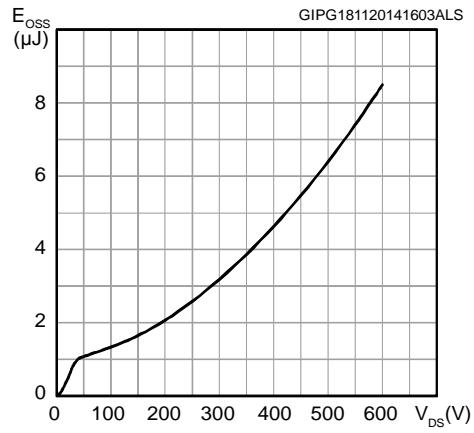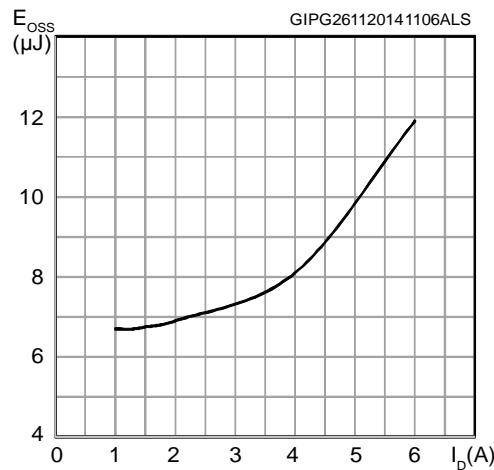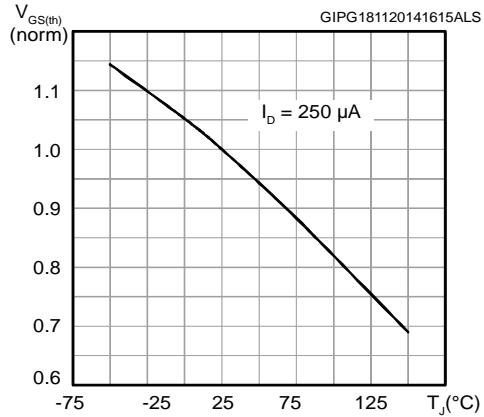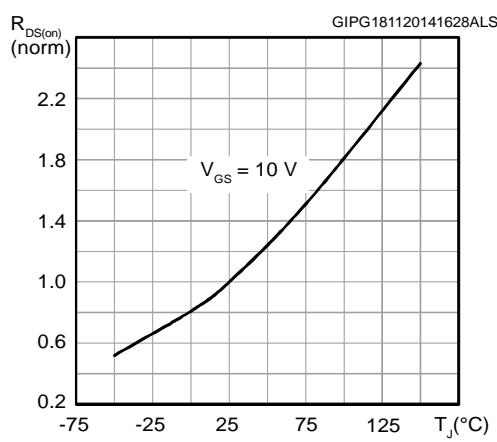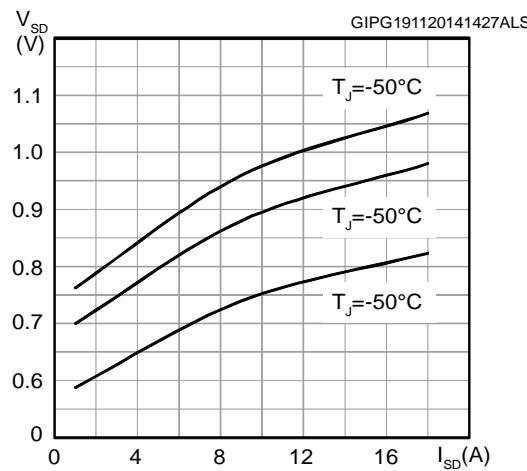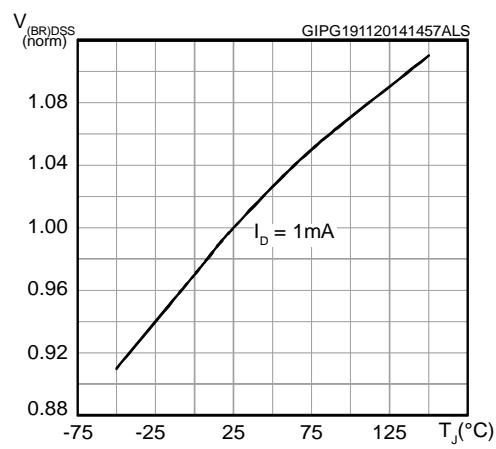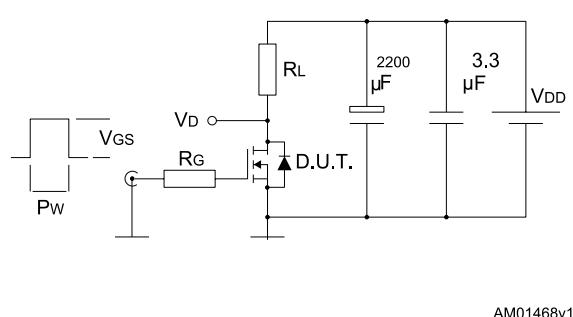
Figure 8: Capacitance variations


Figure 9: Output capacitance stored energy


Figure 10: Turn-off switching loss vs drain current

Figure 11: Normalized gate threshold voltage vs temperature

Figure 12: Normalized on-resistance vs temperature

**Figure 13: Source-drain diode forward characteristics**

Figure 14: Normalized V$_{(BR)DSS}$ vs temperature
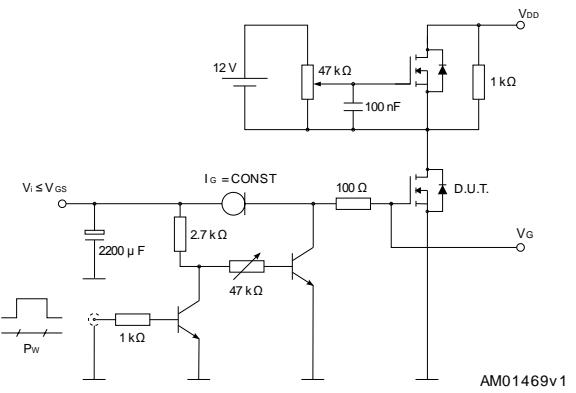
3   Test circuits
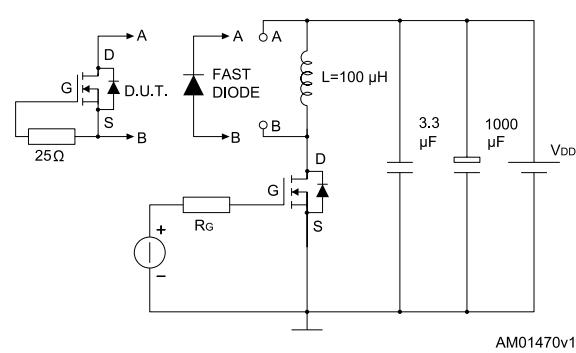
Figure 15: Switching times test circuit for resistive load
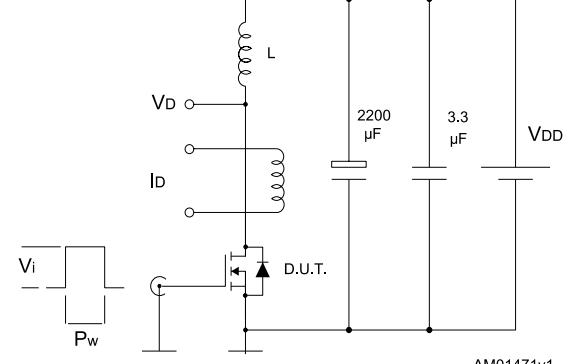
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Figure 16: Gate charge test circuit

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Figure 17: Test circuit for inductive load switching and diode recovery times

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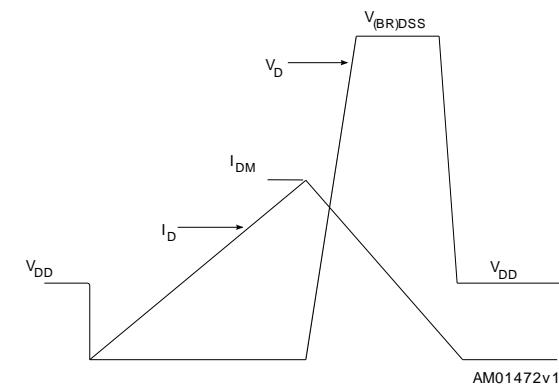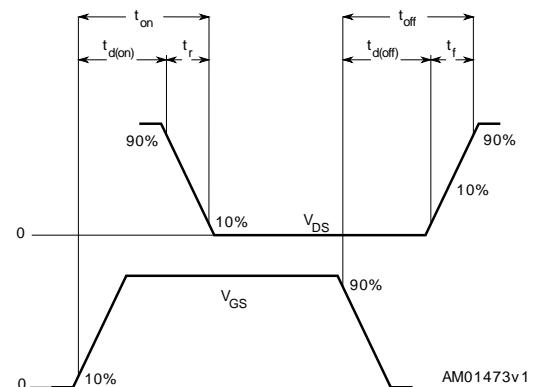
Figure 18: Unclamped inductive load test circuit

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Figure 19: Unclamped inductive waveform

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Figure 20: Switching time waveform

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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

4.1 TO-220 type A package information

Figure 21: TO-220 type A package outline

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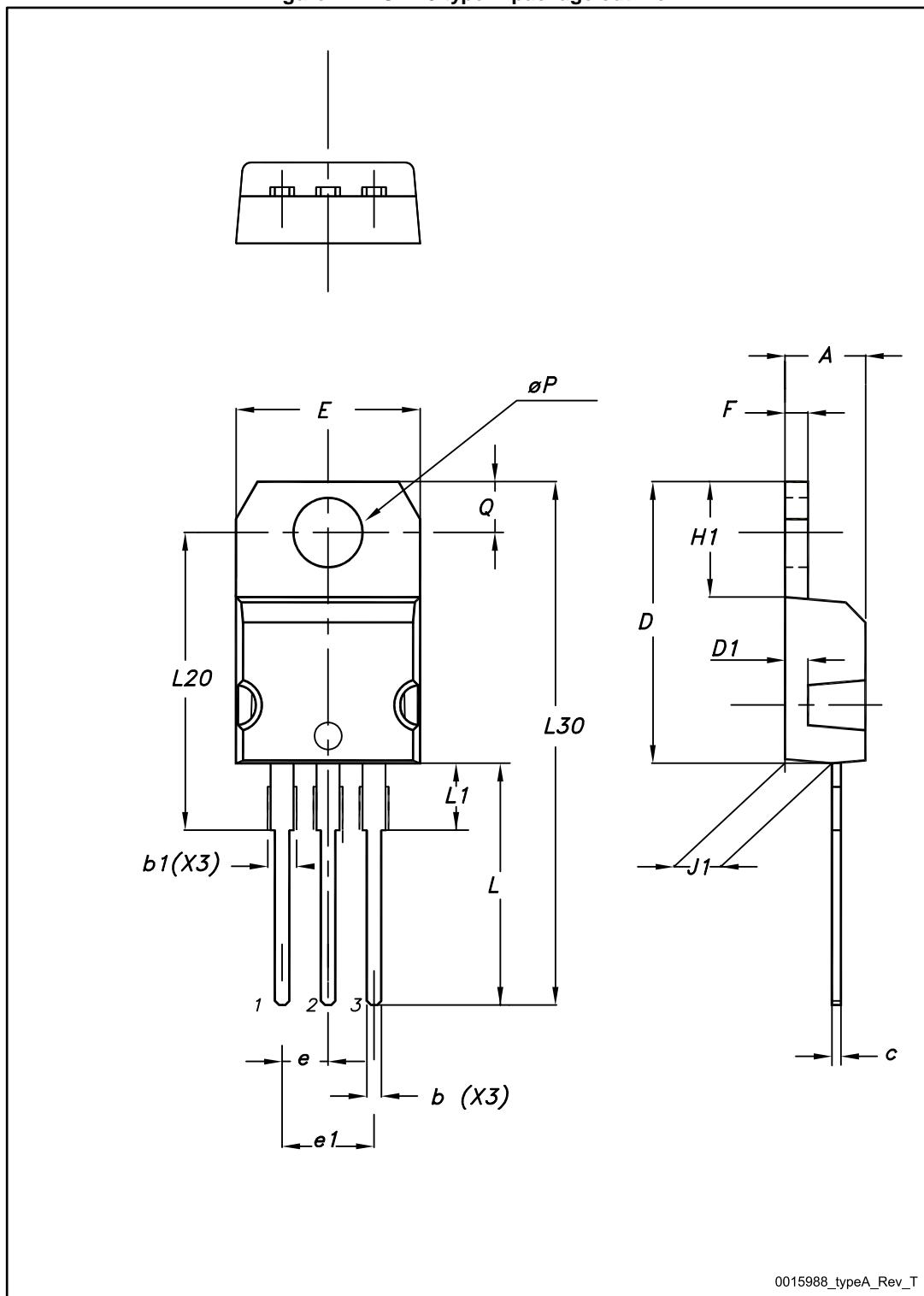
Table 10: TO-220 type A mechanical data

Dim.	mm		
	Min.	**Typ.**	**Max.**
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

5 Revision history

Table 11: Document revision history

Date	Revision	Changes
01-Dec-2014	1	First release.
12-Jan-2015	2	Updated product status from "preliminary data" to "production data".

IMPORTANT NOTICE – PLEASE READ CAREFULLY